

Single N-channel MOSFET

ELM14418AA-N

■ General description

ELM14418AA-N uses advanced trench technology to provide excellent $R_{ds(on)}$, low gate charge and low gate resistance.

■ Features

- $V_{ds}=30V$
- $I_d=11.5A$ ($V_{gs}=20V$)
- $R_{ds(on)} < 14m\Omega$ ($V_{gs}=20V$)
- $R_{ds(on)} < 17m\Omega$ ($V_{gs}=10V$)
- $R_{ds(on)} < 40m\Omega$ ($V_{gs}=4.5V$)

■ Maximum absolute ratings

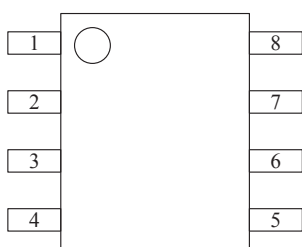
Parameter	Symbol	Limit	Unit	Note	
Drain-source voltage	V_{ds}	30	V		
Gate-source voltage	V_{gs}	± 25	V		
Continuous drain current	I_d	$T_a=25^\circ C$	11.5	A	1
		$T_a=70^\circ C$	9.7		
Pulsed drain current	I_{dm}	40	A	2	
Power dissipation	P_d	$T_a=25^\circ C$	3.0	W	
		$T_a=70^\circ C$	2.1		
Junction and storage temperature range	T_j, T_{stg}	-55 to 150	$^\circ C$		

■ Thermal characteristics

Parameter		Symbol	Typ.	Max.	Unit	Note
Maximum junction-to-ambient	$t \leq 10s$	$R\theta_{ja}$	31	40	$^\circ C/W$	1
Maximum junction-to-ambient	Steady-state		59	75	$^\circ C/W$	
Maximum junction-to-lead	Steady-state	$R\theta_{jl}$	16	24	$^\circ C/W$	3

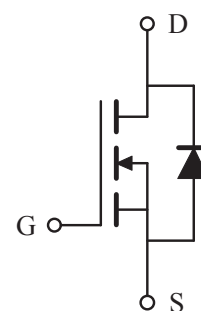
■ Pin configuration

SOP-8(TOP VIEW)



Pin No.	Pin name
1	SOURCE
2	SOURCE
3	SOURCE
4	GATE
5	DRAIN
6	DRAIN
7	DRAIN
8	DRAIN

■ Circuit



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■ Electrical characteristics

T_a=25°C

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
STATIC PARAMETERS						
Drain-source breakdown voltage	BV _{dss}	I _d =250μA, V _{gs} =0V	30			V
Zero gate voltage drain current	I _{dss}	V _{ds} =24V, V _{gs} =0V T _j =55°C			1	μA
					5	
Gate-body leakage current	I _{gss}	V _{ds} =0V, V _{gs} =±25V			100	nA
Gate threshold voltage	V _{gs(th)}	V _{ds} =V _{gs} , I _d =250μA	1.5	2.4	3.0	V
On state drain current	I _{d(on)}	V _{gs} =10V, V _{ds} =5V	40			A
Static drain-source on-resistance	R _{ds(on)}	V _{gs} =20V I _d =11.5A T _j =125°C		9.8	14.0	mΩ
				14.2	18.0	
		V _{gs} =10V, I _d =10A		12.3	17.0	mΩ
		V _{gs} =4.5V, I _d =5A		32.0	40.0	mΩ
Forward transconductance	G _{fs}	V _{ds} =5V, I _d =10A	14	22		S
Diode forward voltage	V _{sd}	I _s =1A, V _{gs} =0V		0.76	1.00	V
Max. body-diode continuous current	I _s				4.3	A
DYNAMIC PARAMETERS						
Input capacitance	C _{iss}			758		pF
Output capacitance	C _{oss}	V _{gs} =0V, V _{ds} =15V, f=1MHz		180		pF
Reverse transfer capacitance	C _{rss}			128		pF
Gate resistance	R _g	V _{gs} =0V, V _{ds} =0V, f=1MHz		0.7		Ω
SWITCHING PARAMETERS						
Total gate charge(10V)	Q _g	V _{gs} =10V, V _{ds} =15V, I _d =11.5A		16.6		nC
Total gate charge(4.5V)	Q _g			8.6		nC
Gate-source charge	Q _{gs}			2.5		nC
Gate-drain charge	Q _{gd}			4.9		nC
Turn-on delay time	t _{d(on)}	V _{gs} =10V, V _{ds} =15V R _l =1.3Ω, R _{gen} =3Ω		5.4		ns
Turn-on rise time	t _r			5.1		ns
Turn-off delay time	t _{d(off)}			14.4		ns
Turn-off fall time	t _f			3.7		ns
Body diode reverse recovery time	t _{rr}		I _f =11.5A, dI/dt=100A/μs		16.9	
Body diode reverse recovery charge	Q _{rr}	I _f =11.5A, dI/dt=100A/μs		6.6		nC

NOTE :

1. The value of R_{θja} is measured with the device mounted on 1in² FR-4 board of 2oz. Copper, in still air environment with T_a=25°C. The value in any given applications depends on the user's specific board design, The current rating is based on the t ≤ 10s thermal resistance rating.
2. Repetitive rating, pulse width limited by junction temperature.
3. The R_{θja} is the sum of the thermal impedance from junction to lead R_{θjl} and lead to ambient.
4. The static characteristics in Figures 1 to 6 are obtained using 80μs pulses, duty cycle 0.5%max.
5. These tests are performed with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_a=25°C. The SOA curve provides a single pulse rating.

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■ Typical electrical and thermal characteristics

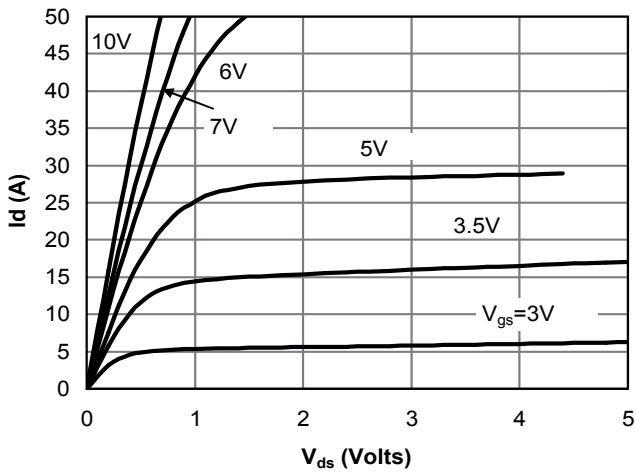


Fig 1: On-Region Characteristics

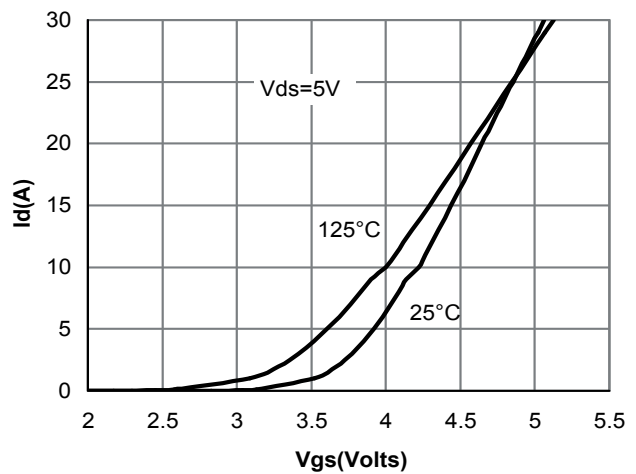


Figure 2: Transfer Characteristics

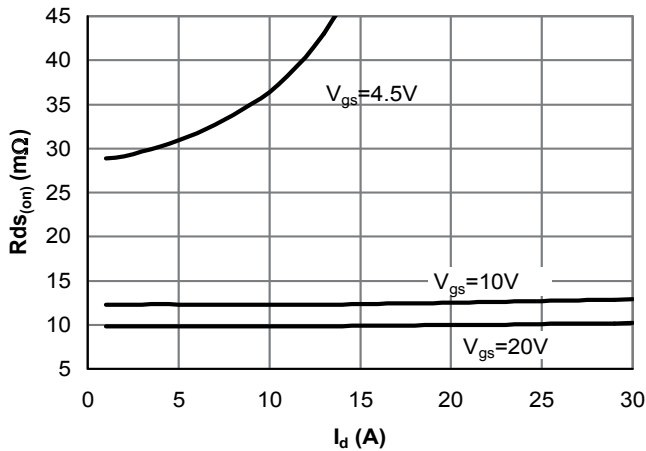


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

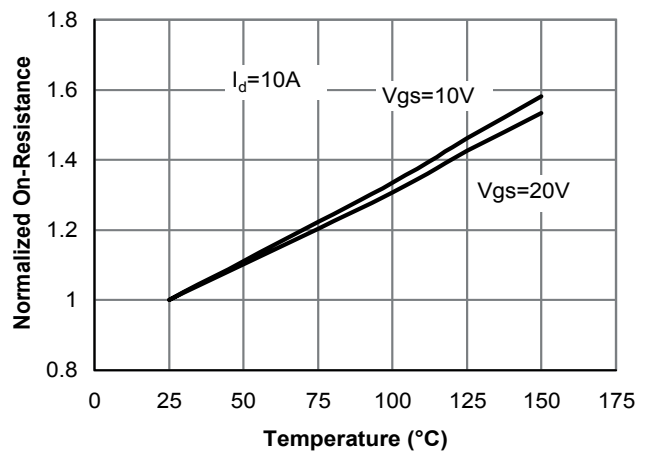


Figure 4: On-Resistance vs. Junction Temperature

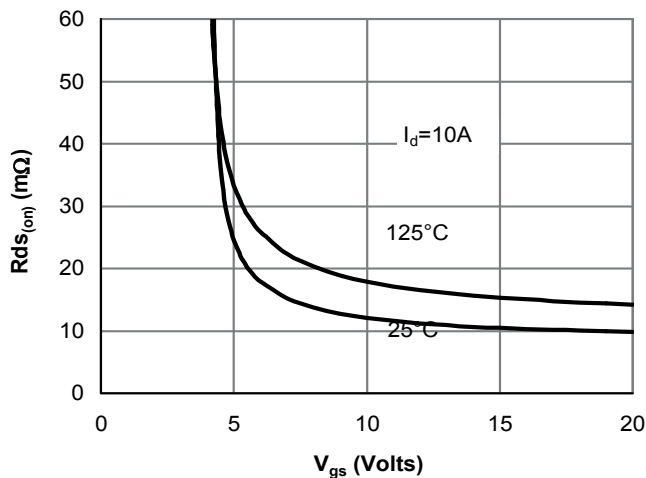


Figure 5: On-Resistance vs. Gate-Source Voltage

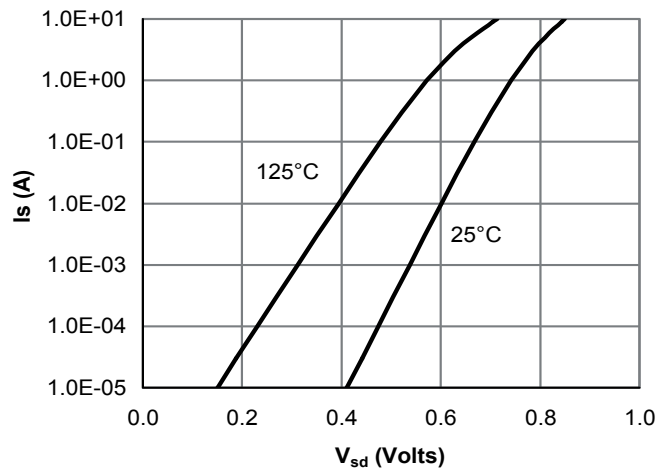


Figure 6: Body-Diode Characteristics

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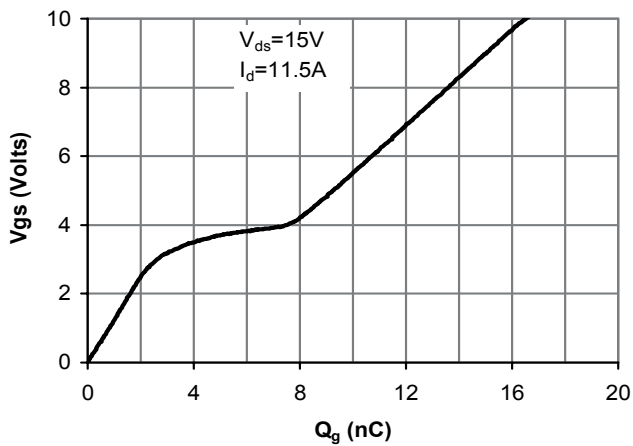


Figure 7: Gate-Charge Characteristics

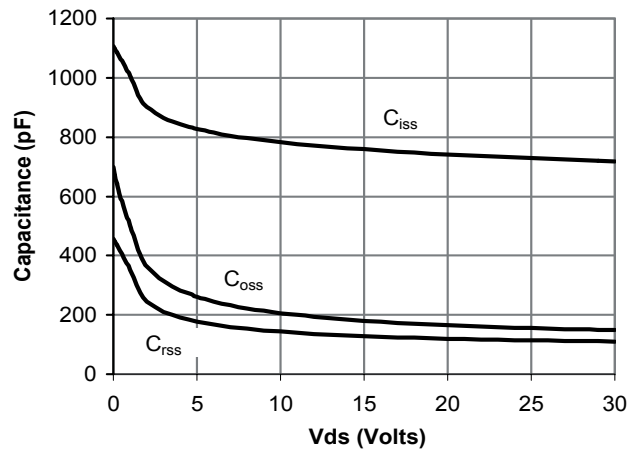


Figure 8: Capacitance Characteristics

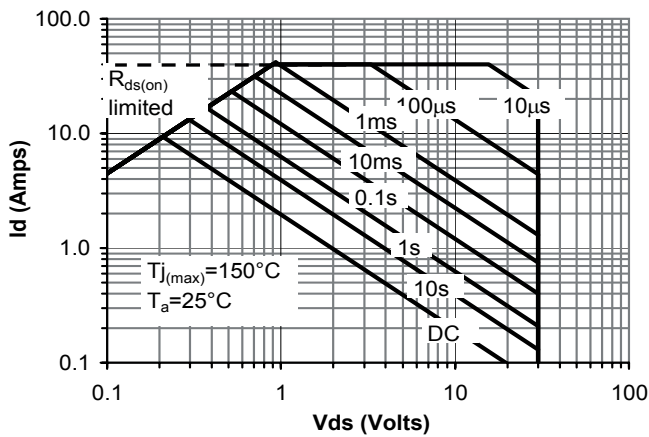


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

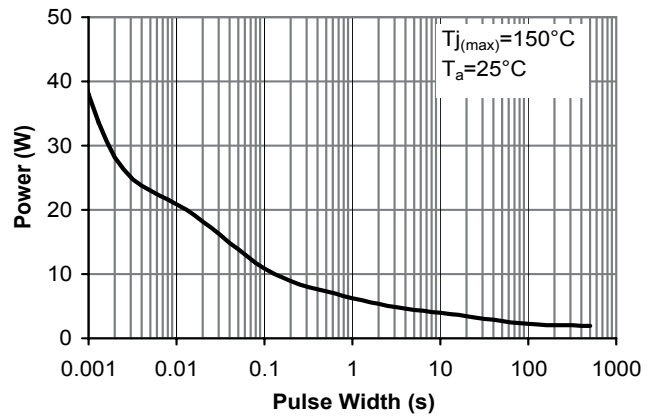


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

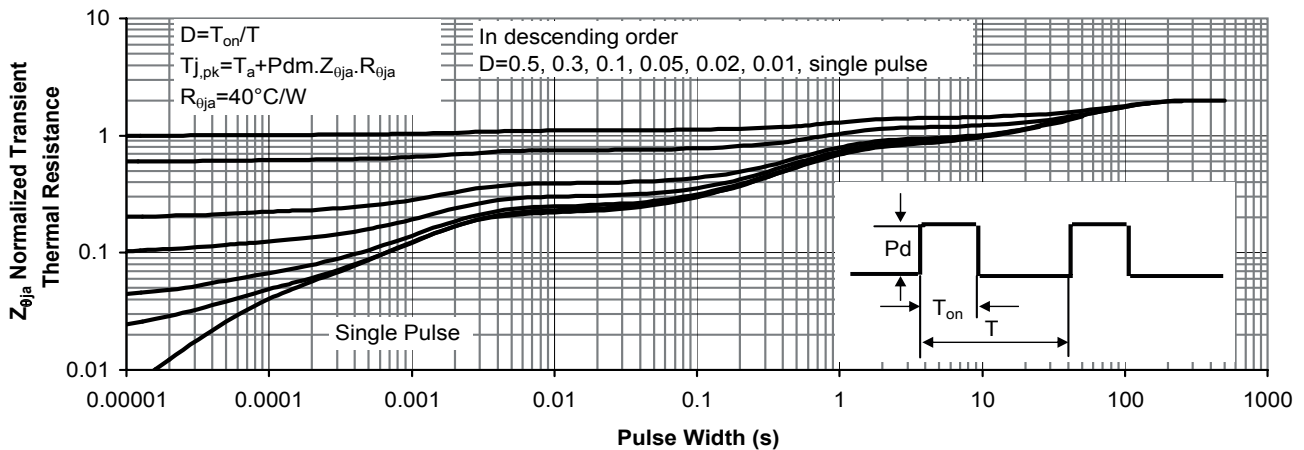


Figure 11: Normalized Maximum Transient Thermal Impedance